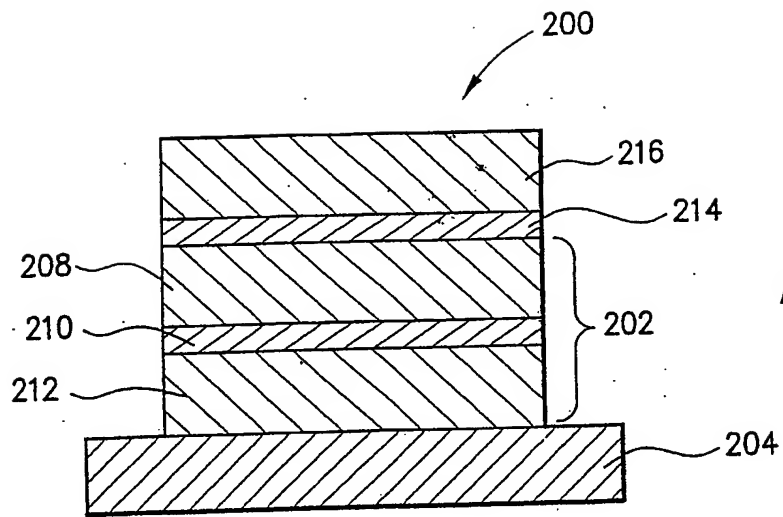
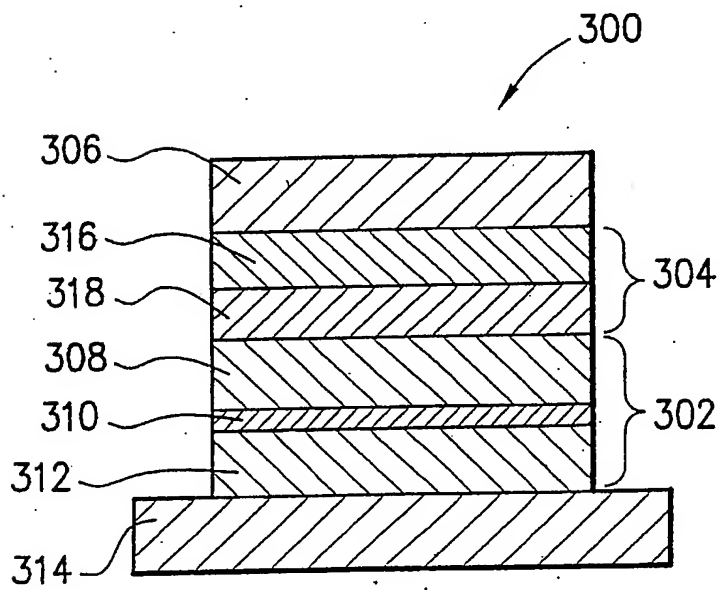
**Fig. 1**

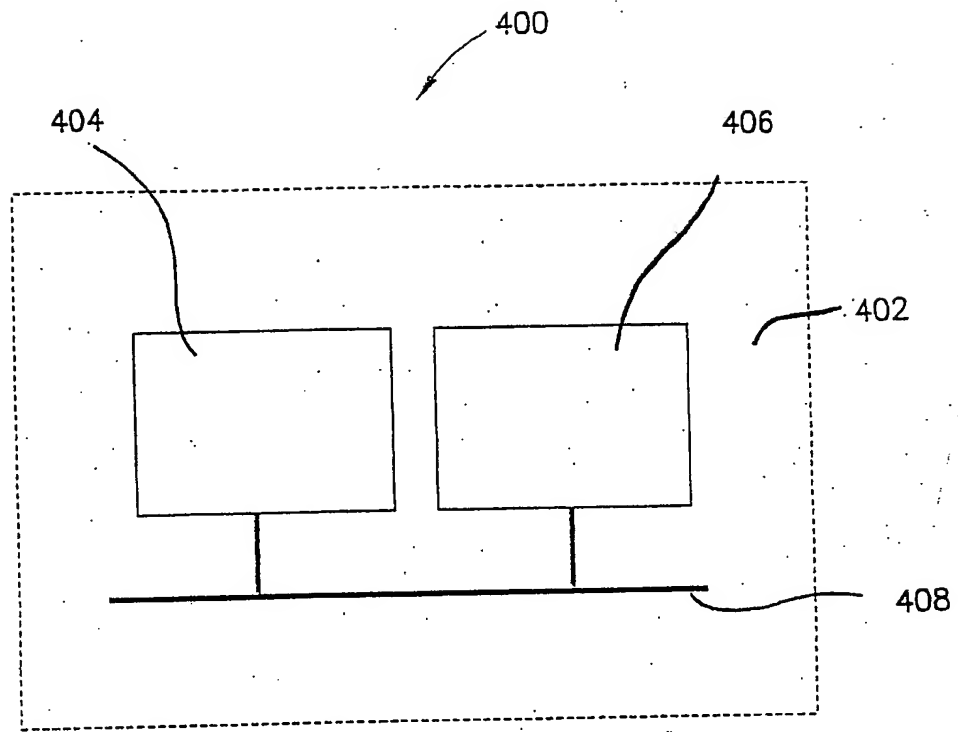


**Fig. 2**



**Fig. 3**

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**Fig. 4**

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HEATING MRAM CELLS OF AN ARRAY OF  
MRAM CELLS, THE MRAM CELLS BEING  
SWITCHABLE BETWEEN TWO STATES UNDER  
THE INFLUENCE OF A MAGNETIC FIELD,  
EACH MRAM CELL COMPRISING A  
REFERENCE LAYER AND A DATA LAYER,  
THE REFERENCE LAYER HAVING A LOWER  
COERCIVITY THAN THE DATA LAYER

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UTILIZING THE GENERATED HEAT TO  
FACILITATE CELL STATE SWITCHING OF  
MEMORY CELLS

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**Fig. 5**